

General Description

The AO4902 uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. The two identical MOSFETs are co-packaged in parallel with a Schottky diode, making them ideal for many bridge and totem pole applications, for e.g. DDR memory. *Standard Product AO4902 is Pb-free (meets ROHS & Sony 259 specifications). AO4902L is a Green Product ordering option. AO4902 and AO4902L are electrically identical.*

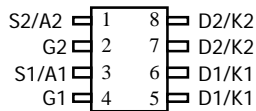
Features

- V_{DS} (V) = 30V
- I_D = 6.9A (V_{GS} = 10V)
- $R_{DS(ON)}$ < 27m Ω (V_{GS} = 10V)
- $R_{DS(ON)}$ < 32m Ω (V_{GS} = 4.5V)
- $R_{DS(ON)}$ < 50m Ω (V_{GS} = 2.5V)

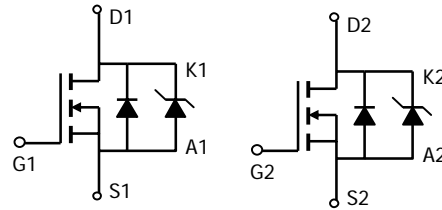


SCHOTTKY

V_{DS} (V) = 30V, I_F = 3A, V_F = 0.5V@1A



SOIC-8



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	MOSFET	Schottky	Units
Drain-Source Voltage	V_{DS}	30		V
Gate-Source Voltage	V_{GS}	± 12		V
Continuous Drain Current ^A	I_D	$T_A=25^\circ\text{C}$	6.9	A
		$T_A=70^\circ\text{C}$	5.8	
Pulsed Drain Current ^B	I_{DM}	40		
Schottky reverse voltage	V_{KA}		30	V
Continuous Forward Current ^A	I_F	$T_A=25^\circ\text{C}$	3	A
		$T_A=70^\circ\text{C}$	2	
Pulsed Forward Current ^B	I_{FM}		40	
Power Dissipation	P_D	$T_A=25^\circ\text{C}$	2	W
		$T_A=70^\circ\text{C}$	1.44	
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	-55 to 150	$^\circ\text{C}$

Parameter: Thermal Characteristics MOSFET		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$t \leq 10\text{s}$	$R_{\theta JA}$	48	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A	Steady-State		74	110	
Maximum Junction-to-Lead ^C	Steady-State	$R_{\theta JL}$	35	40	
Thermal Characteristics Schottky					
Maximum Junction-to-Ambient ^A	$t \leq 10\text{s}$	$R_{\theta JA}$	47.5	62.5	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A	Steady-State		71	110	
Maximum Junction-to-Lead ^C	Steady-State	$R_{\theta JL}$	32	40	

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
V _{DS}	Drain-Source Breakdown Voltage	I _D =250μA, V _{GS} =0V	30			V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =24V, V _{GS} =0V T _J =55°C			1 5	μA
I _{GSS}	Gate-Body leakage current	V _{DS} =0V, V _{GS} = ±12V			100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} I _D =250μA	0.7	1	1.4	V
I _{D(ON)}	On state drain current	V _{GS} =4.5V, V _{DS} =5V	25			A
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =10V, I _D =6.9A T _J =125°C		22.6 33	27 40	mΩ
		V _{GS} =4.5V, I _D =6.0A		27	32	
		V _{GS} =2.5V, I _D =5A		42	50	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =5A	12	16		S
V _{SD}	Diode Forward Voltage	I _S =1A		0.71	1	V
I _S	Maximum Body-Diode Continuous Current				3	A
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =15V, f=1MHz		846	1050	pF
C _{oss}	Output Capacitance			96		pF
C _{rss}	Reverse Transfer Capacitance			67		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		1.24	3.6	Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =15V, I _D =6.9A		9.6	12	nC
Q _{gs}	Gate Source Charge			1.65		nC
Q _{gd}	Gate Drain Charge			3		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =10V, V _{DS} =15V, R _L =2.2Ω, R _{GEN} =3Ω		3.2	4.8	ns
t _r	Turn-On Rise Time			4.5	6.8	ns
t _{D(off)}	Turn-Off DelayTime			26.3	40	ns
t _f	Turn-Off Fall Time			4.8	7	ns
t _{rr}	Body Diode Reverse Recovery time	I _F =5A, dI/dt=100A/μs		15.5	20	ns
Q _{rr}	Body Diode Reverse Recovery charge	I _F =5A, dI/dt=100A/μs		7.9		nC
SCHOTTKY PARAMETERS						
V _F	Forward Voltage Drop	I _F =1.0A		0.45	0.5	V
I _{rm}	Maximum reverse leakage current	V _R =30V		0.007	0.05	mA
		V _R =30V, T _J =125°C		3.2	10	
		V _R =30V, T _J =150°C		12	20	
C _T	Junction Capacitance	V _R =15V		37		pF

A: The value of R_{θJA} is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design. The current rating is based on the t ≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C: The R_{θJA} is the sum of the thermal impedance from junction to lead R_{θJL} and lead to ambient.

D: The static characteristics in Figures 1 to 6,12,14 are obtained using 80 μs pulses, duty cycle 0.5% max.

E: These tests are performed with the device mounted on 1 in² FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

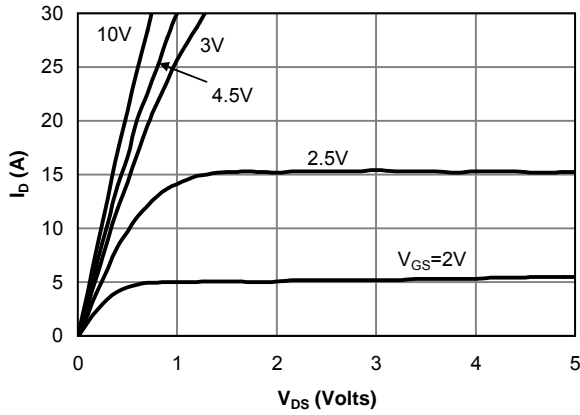


Fig 1: On-Region Characteristics

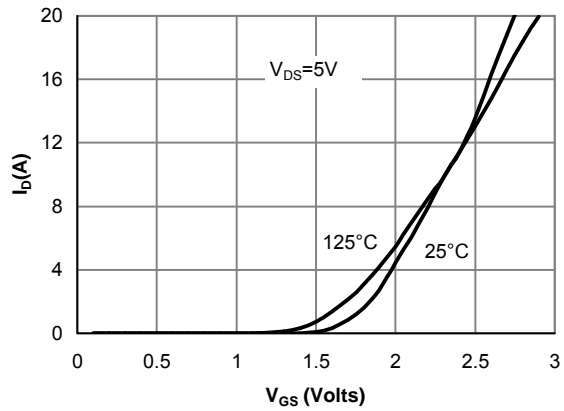


Figure 2: Transfer Characteristics

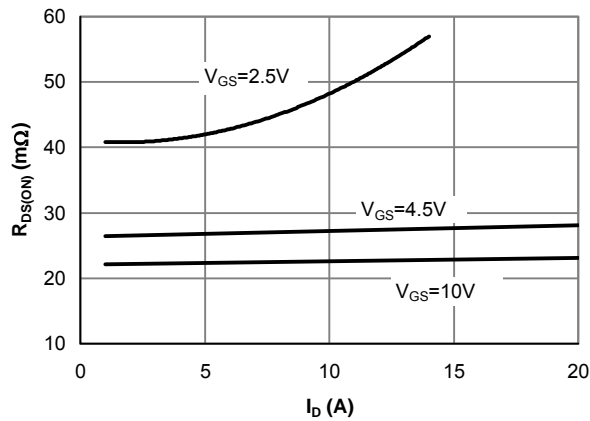


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

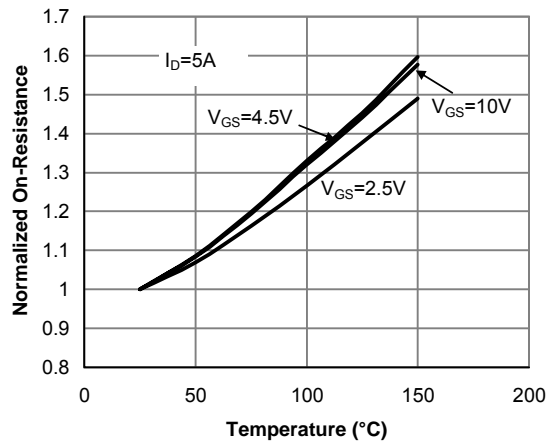


Figure 4: On resistance vs. Junction Temperature

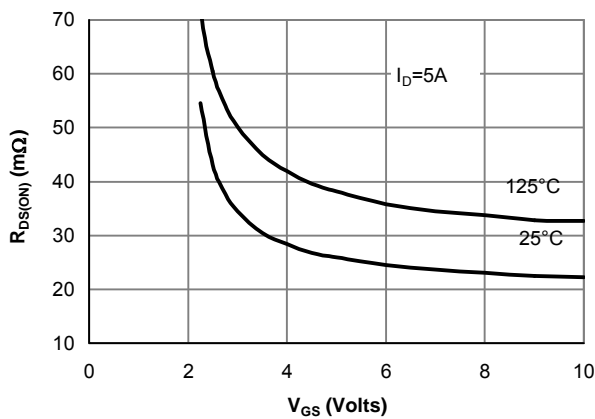


Figure 5: On resistance vs. Gate-Source Voltage

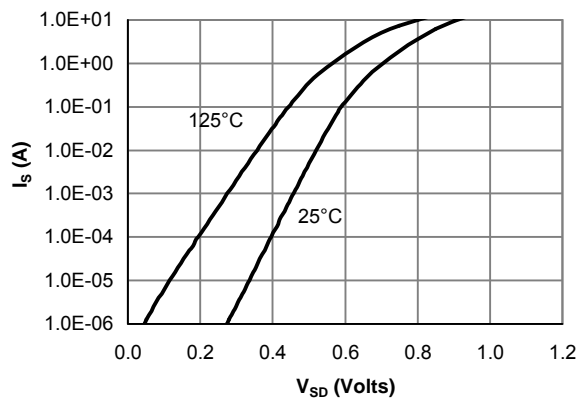


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

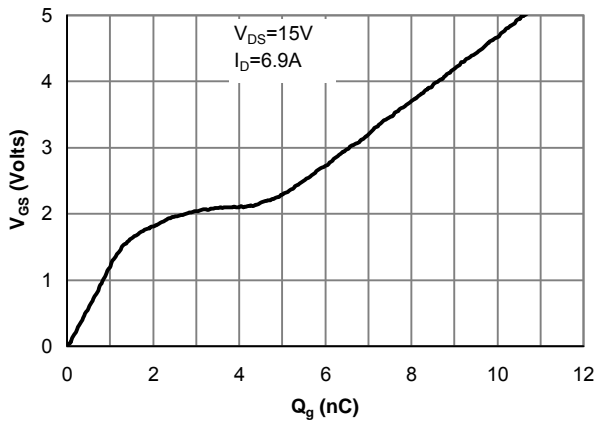


Figure 7: Gate-Charge Characteristics

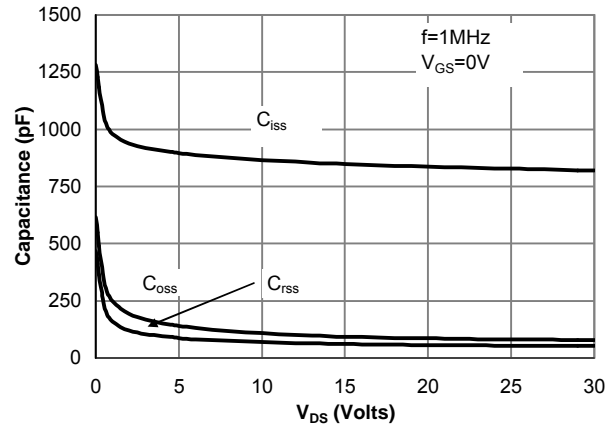


Figure 8: Capacitance Characteristics

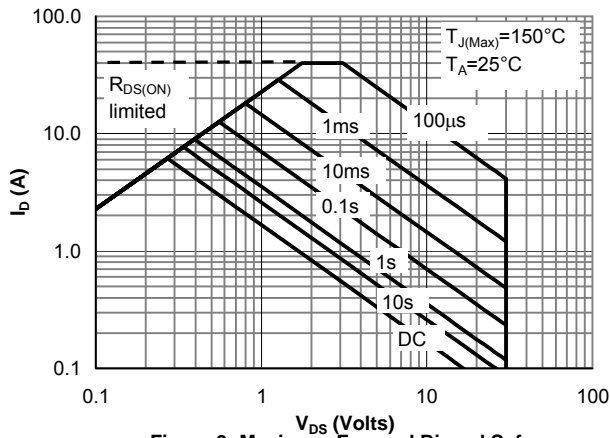


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

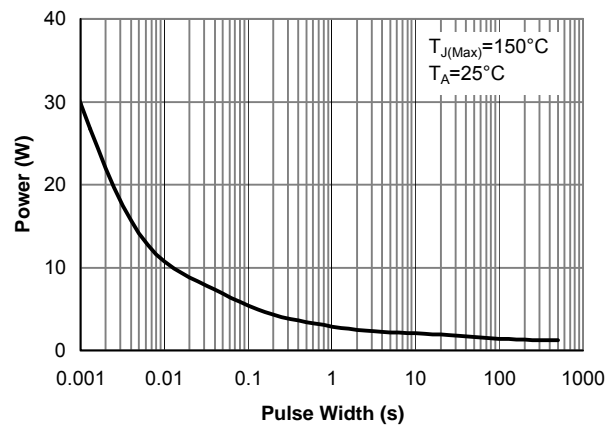


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

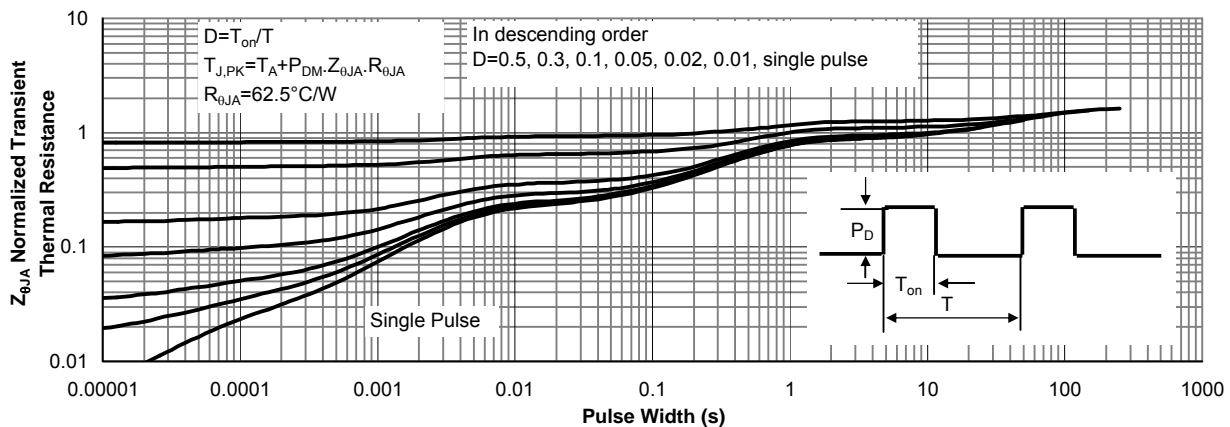


Figure 11: Normalized Maximum Transient Thermal Impedance

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS: SCHOTTKY

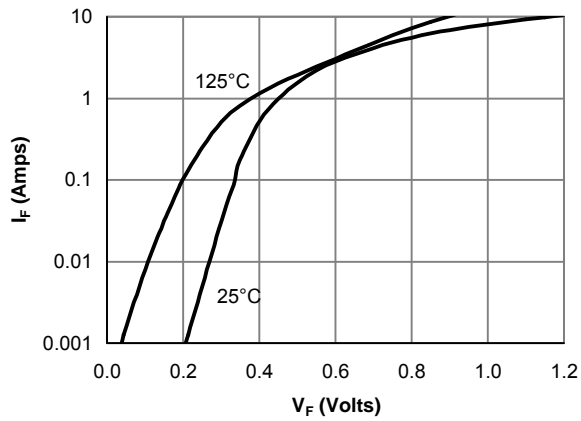


Figure 12: Schottky Forward Characteristics

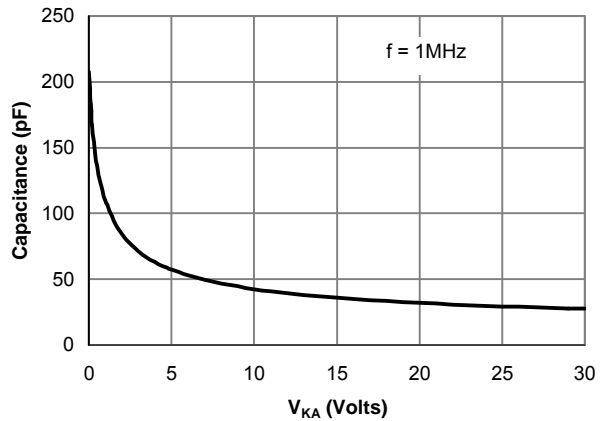


Figure 13: Schottky Capacitance Characteristics

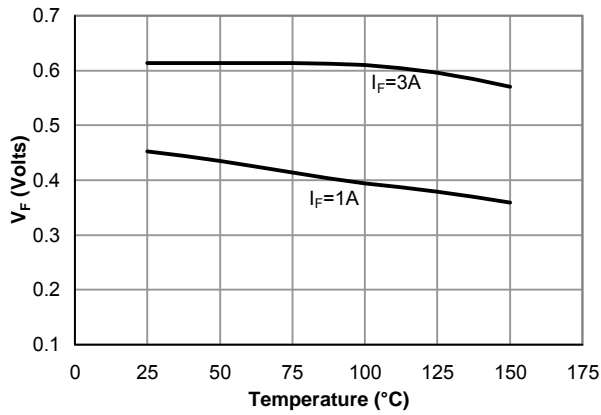


Figure 14: Schottky Forward Drop vs. Junction Temperature

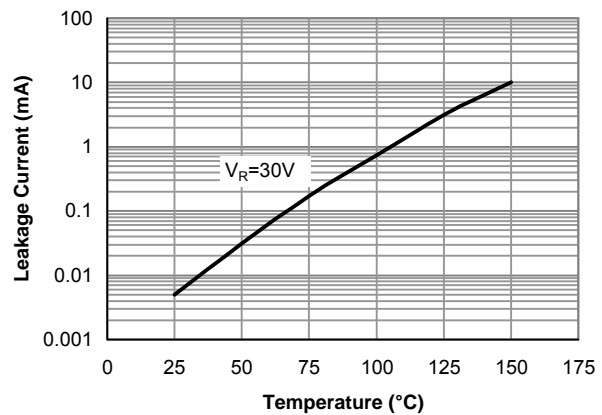


Figure 15: Schottky Leakage current vs. Junction Temperature

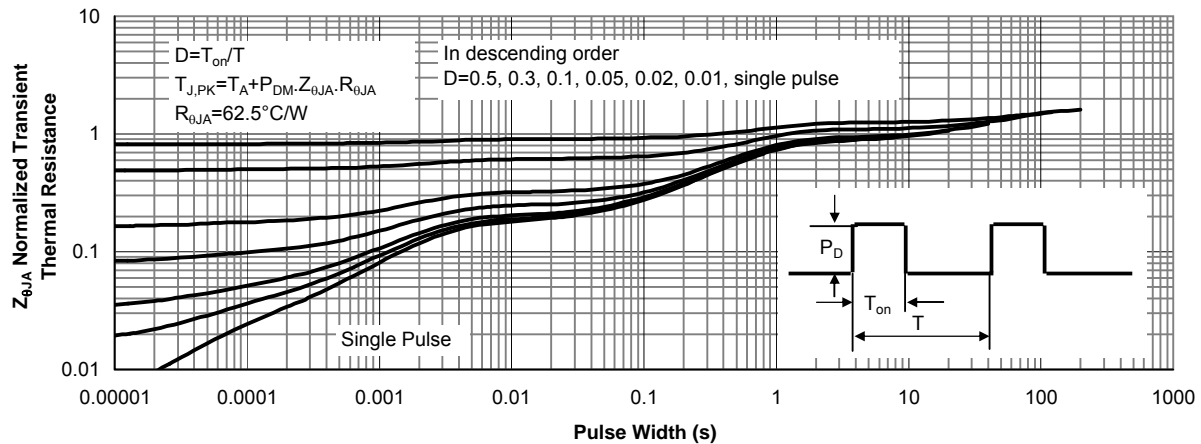


Figure 15: Schottky Normalized Maximum Transient Thermal Impedance